

<b>Notic of References Cit d</b>	Application/Control No. 10/039,484	Applicant(s)/Patent Under Reexamination DENG ET AL.	
	Examiner Johannes P Mondt	Art Unit 2826	Page 1 of 1

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	M	US-			

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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